

## ADD-A-PAK Generation VII Power Modules

### Thyristor/Thyristor, 45 A/60 A



ADD-A-PAK

#### PRODUCT SUMMARY

|             |                               |
|-------------|-------------------------------|
| $I_{T(AV)}$ | 45 A/60 A                     |
| Type        | Modules - Thyristor, Standard |

#### MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

#### FEATURES

- High voltage
- Industrial standard package
- Low thermal resistance
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT

#### BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

#### ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

#### MAJOR RATINGS AND CHARACTERISTICS

| SYMBOL        | CHARACTERISTICS | VS-VSK.41   | VS-VSK.56   | UNITS              |
|---------------|-----------------|-------------|-------------|--------------------|
| $I_{T(AV)}$   | 85 °C           | 45          | 60          | A                  |
| $I_{T(RMS)}$  |                 | 70          | 95          |                    |
| $I_{TSM}$     | 50 Hz           | 850         | 1200        |                    |
|               | 60 Hz           | 890         | 1256        |                    |
| $I^2t$        | 50 Hz           | 3.61        | 7.20        | kA <sup>2</sup> s  |
|               | 60 Hz           | 3.30        | 6.57        |                    |
| $I^2\sqrt{t}$ |                 | 36.1        | 72          | kA <sup>2</sup> √s |
| $V_{RRM}$     | Range           | 400 to 1600 | 400 to 1600 | V                  |
| $T_{Stg}$     |                 | -40 to 125  |             | °C                 |
| $T_J$         |                 | -40 to 125  |             | °C                 |



## ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS        |              |                                                                 |                                                                     |                                                                                      |                                                     |
|------------------------|--------------|-----------------------------------------------------------------|---------------------------------------------------------------------|--------------------------------------------------------------------------------------|-----------------------------------------------------|
| TYPE NUMBER            | VOLTAGE CODE | V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE<br>V | V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE<br>V | V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT<br>V | I <sub>RRM</sub> , I <sub>DRM</sub> AT 125 °C<br>mA |
| VS-VSK.41<br>VS-VSK.56 | 04           | 400                                                             | 500                                                                 | 400                                                                                  | 15                                                  |
|                        | 08           | 800                                                             | 900                                                                 | 800                                                                                  |                                                     |
|                        | 12           | 1200                                                            | 1300                                                                | 1200                                                                                 |                                                     |
|                        | 16           | 1600                                                            | 1700                                                                | 1600                                                                                 |                                                     |

| ON-STATE CONDUCTION                                      |                                   |                                                                                                                                                                         |                                         |                                                                       |           |           |                    |
|----------------------------------------------------------|-----------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------|-----------------------------------------------------------------------|-----------|-----------|--------------------|
| PARAMETER                                                | SYMBOL                            | TEST CONDITIONS                                                                                                                                                         |                                         |                                                                       | VS-VSK.41 | VS-VSK.56 | UNITS              |
| Maximum average on-state current                         | I <sub>T(AV)</sub>                | 180° conduction, half sine wave, T <sub>C</sub> = 85 °C                                                                                                                 |                                         |                                                                       | 45        | 60        | A                  |
| Maximum continuous RMS on-state current                  | I <sub>T(RMS)</sub>               | DC                                                                                                                                                                      |                                         |                                                                       | 70        | 95        |                    |
|                                                          |                                   | T <sub>C</sub>                                                                                                                                                          |                                         |                                                                       | 82        | 81        | °C                 |
| Maximum peak, one-cycle non-repetitive on-state current  | I <sub>TSM</sub>                  | t = 10 ms                                                                                                                                                               | No voltage reapplied                    | Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum | 850       | 1200      | A                  |
|                                                          |                                   | t = 8.3 ms                                                                                                                                                              |                                         |                                                                       | 890       | 1256      |                    |
|                                                          |                                   | t = 10 ms                                                                                                                                                               | 100 % V <sub>RRM</sub> reapplied        |                                                                       | 715       | 1000      |                    |
|                                                          |                                   | t = 8.3 ms                                                                                                                                                              |                                         |                                                                       | 750       | 1056      |                    |
| Maximum I <sup>2</sup> t for fusing                      | I <sup>2</sup> t                  | t = 10 ms                                                                                                                                                               | No voltage reapplied                    | Initial T <sub>J</sub> = T <sub>J</sub> maximum                       | 3.61      | 7.20      | kA <sup>2</sup> s  |
|                                                          |                                   | t = 8.3 ms                                                                                                                                                              |                                         |                                                                       | 3.30      | 6.57      |                    |
|                                                          |                                   | t = 10 ms                                                                                                                                                               | 100 % V <sub>RRM</sub> reapplied        |                                                                       | 2.56      | 5.10      |                    |
|                                                          |                                   | t = 8.3 ms                                                                                                                                                              |                                         |                                                                       | 2.33      | 4.56      |                    |
| Maximum I <sup>2</sup> √t for fusing                     | I <sup>2</sup> √t <sup>(1)</sup>  | t = 0.1 ms to 10 ms, no voltage reapplied<br>T <sub>J</sub> = T <sub>J</sub> maximum                                                                                    |                                         |                                                                       | 36.1      | 72        | kA <sup>2</sup> √s |
| Maximum value of threshold voltage                       | V <sub>T(TO)</sub> <sup>(2)</sup> | Low level <sup>(3)</sup>                                                                                                                                                | T <sub>J</sub> = T <sub>J</sub> maximum |                                                                       | 1.08      | 0.91      | V                  |
|                                                          |                                   | High level <sup>(4)</sup>                                                                                                                                               |                                         |                                                                       | 1.12      | 1.02      |                    |
| Maximum value of on-state slope resistance               | r <sub>t</sub> <sup>(2)</sup>     | Low level <sup>(3)</sup>                                                                                                                                                | T <sub>J</sub> = T <sub>J</sub> maximum |                                                                       | 4.7       | 4.27      | mΩ                 |
|                                                          |                                   | High level <sup>(4)</sup>                                                                                                                                               |                                         |                                                                       | 4.5       | 3.77      |                    |
| Maximum on-state voltage drop                            | V <sub>TM</sub>                   | I <sub>TM</sub> = π x I <sub>T(AV)</sub>                                                                                                                                | T <sub>J</sub> = 25 °C                  |                                                                       | 1.81      | 1.7       | V                  |
| Maximum non-repetitive rate of rise of turned on current | di/dt                             | T <sub>J</sub> = 25 °C, from 0.67 V <sub>DRM</sub> , I <sub>TM</sub> = π x I <sub>T(AV)</sub> , I <sub>g</sub> = 500 mA, t <sub>r</sub> < 0.5 μs, t <sub>p</sub> > 6 μs |                                         |                                                                       | 150       |           | A/μs               |
| Maximum holding current                                  | I <sub>H</sub>                    | T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit                                                                                           |                                         |                                                                       | 200       |           | mA                 |
| Maximum latching current                                 | I <sub>L</sub>                    | T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load                                                                                                              |                                         |                                                                       | 400       |           |                    |

### Notes

(1) I<sup>2</sup>t for time t<sub>x</sub> = I<sup>2</sup>√t × √t<sub>x</sub>

(2) Average power = V<sub>T(TO)</sub> × I<sub>T(AV)</sub> + r<sub>t</sub> × (I<sub>T(RMS)</sub>)<sup>2</sup>

(3) 16.7 % × π × I<sub>AV</sub> < I < π × I<sub>AV</sub>

(4) I > π × I<sub>AV</sub>



| TRIGGERING                                 |                    |                                                         |                                      |           |           |       |
|--------------------------------------------|--------------------|---------------------------------------------------------|--------------------------------------|-----------|-----------|-------|
| PARAMETER                                  | SYMBOL             | TEST CONDITIONS                                         |                                      | VS-VSK.41 | VS-VSK.56 | UNITS |
| Maximum peak gate power                    | P <sub>GM</sub>    |                                                         |                                      | 10        |           | W     |
| Maximum average gate power                 | P <sub>G(AV)</sub> |                                                         |                                      | 2.5       |           |       |
| Maximum peak gate current                  | I <sub>GM</sub>    |                                                         |                                      | 2.5       |           | A     |
| Maximum peak negative gate voltage         | - V <sub>GM</sub>  |                                                         |                                      | 10        |           | V     |
| Maximum gate voltage required to trigger   | V <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                | Anode supply = 6 V<br>resistive load | 4.0       |           |       |
|                                            |                    | T <sub>J</sub> = 25 °C                                  |                                      | 2.5       |           |       |
|                                            |                    | T <sub>J</sub> = 125 °C                                 |                                      | 1.7       |           |       |
| Maximum gate current required to trigger   | I <sub>GT</sub>    | T <sub>J</sub> = - 40 °C                                | Anode supply = 6 V<br>resistive load | 270       |           | mA    |
|                                            |                    | T <sub>J</sub> = 25 °C                                  |                                      | 150       |           |       |
|                                            |                    | T <sub>J</sub> = 125 °C                                 |                                      | 80        |           |       |
| Maximum gate voltage that will not trigger | V <sub>GD</sub>    | T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied |                                      | 0.25      |           | V     |
| Maximum gate current that will not trigger | I <sub>GD</sub>    | T <sub>J</sub> = 125 °C, rated V <sub>DRM</sub> applied |                                      | 6         |           | mA    |

| BLOCKING                                                                    |                          |                                                                       |                            |           |            |
|-----------------------------------------------------------------------------|--------------------------|-----------------------------------------------------------------------|----------------------------|-----------|------------|
| PARAMETER                                                                   | SYMBOL                   | TEST CONDITIONS                                                       | VS-VSK.41                  | VS-VSK.56 | UNITS      |
| Maximum peak reverse and off-state leakage current at $V_{RRM}$ , $V_{DRM}$ | $I_{RRM}$ ,<br>$I_{DRM}$ | $T_J = 125\text{ }^{\circ}\text{C}$ , gate open circuit               | 15                         |           | mA         |
| Maximum RMS insulation voltage                                              | $V_{INS}$                | 50 Hz                                                                 | 3000 (1 min)<br>3600 (1 s) |           | V          |
| Maximum critical rate of rise of off-state voltage                          | dV/dt                    | $T_J = 125\text{ }^{\circ}\text{C}$ , linear to $0.67\text{ }V_{DRM}$ | 1000                       |           | V/ $\mu$ s |

| THERMAL AND MECHANICAL SPECIFICATIONS                         |                                   |                                                                                                                                          |                        |           |       |
|---------------------------------------------------------------|-----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------|------------------------|-----------|-------|
| PARAMETER                                                     | SYMBOL                            | TEST CONDITIONS                                                                                                                          | VS-VSK.41              | VS-VSK.56 | UNITS |
| Junction operating and storage temperature range              | T <sub>J</sub> , T <sub>Stg</sub> |                                                                                                                                          | -40 to 125             |           | °C    |
| Maximum internal thermal resistance, junction to case per leg | R <sub>thJC</sub>                 | DC operation                                                                                                                             | 0.44                   | 0.35      | °C/W  |
| Typical thermal resistance, case to heatsink per module       | R <sub>thCS</sub>                 | Mounting surface flat, smooth and greased                                                                                                | 0.1                    |           |       |
| Mounting torque ± 10 %                                        | to heatsink                       | A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound. | 4                      |           | Nm    |
|                                                               | busbar                            |                                                                                                                                          | 3                      |           |       |
| Approximate weight                                            |                                   |                                                                                                                                          | 75                     |           | g     |
|                                                               |                                   |                                                                                                                                          | 2.7                    |           | oz.   |
| Case style                                                    |                                   | JEDEC®                                                                                                                                   | AAP GEN VII (TO-240AA) |           |       |

| ΔR CONDUCTION PER JUNCTION |                           |       |       |       |       |                             |       |       |       |       |       |
|----------------------------|---------------------------|-------|-------|-------|-------|-----------------------------|-------|-------|-------|-------|-------|
| DEVICES                    | SINE HALF WAVE CONDUCTION |       |       |       |       | RECTANGULAR WAVE CONDUCTION |       |       |       |       | UNITS |
|                            | 180°                      | 120°  | 90°   | 60°   | 30°   | 180°                        | 120°  | 90°   | 60°   | 30°   |       |
| VSK.41..                   | 0.110                     | 0.131 | 0.17  | 0.23  | 0.342 | 0.085                       | 0.138 | 0.177 | 0.235 | 0.345 | °C/W  |
| VSK.56..                   | 0.088                     | 0.104 | 0.134 | 0.184 | 0.273 | 0.07                        | 0.111 | 0.143 | 0.189 | 0.275 |       |

#### Note

- Table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC

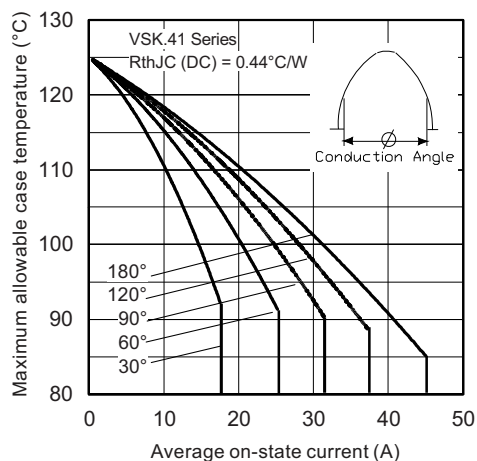


Fig. 1 - Current Ratings Characteristics

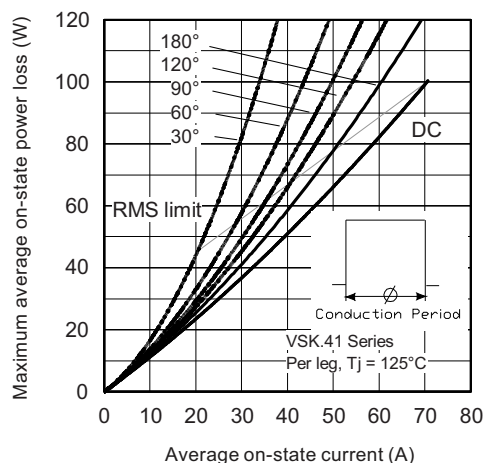


Fig. 4 - On-State Power Loss Characteristics

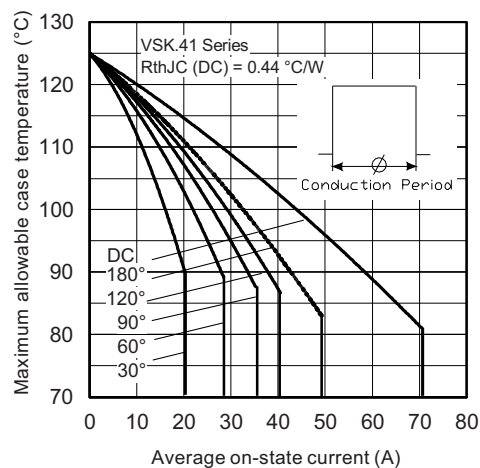


Fig. 2 - Current Ratings Characteristics

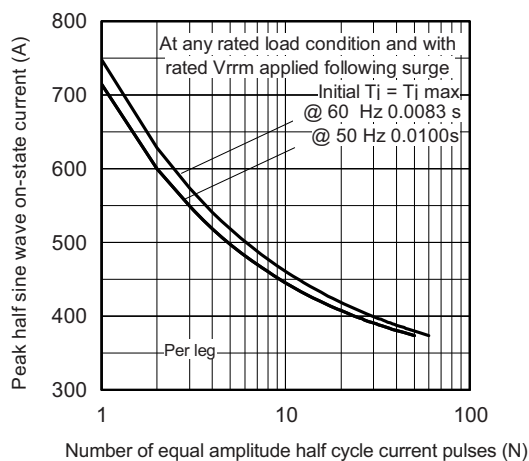


Fig. 5 - Maximum Non-Repetitive Surge Current

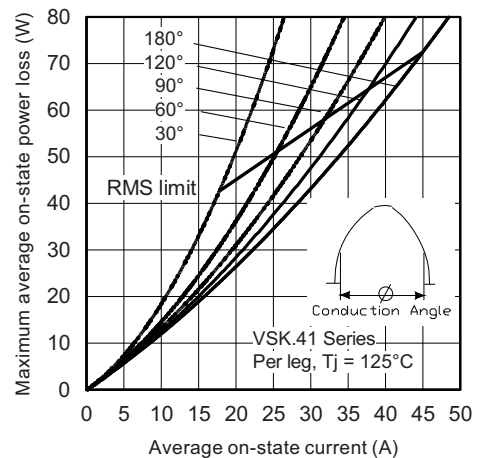


Fig. 3 - On-State Power Loss Characteristics

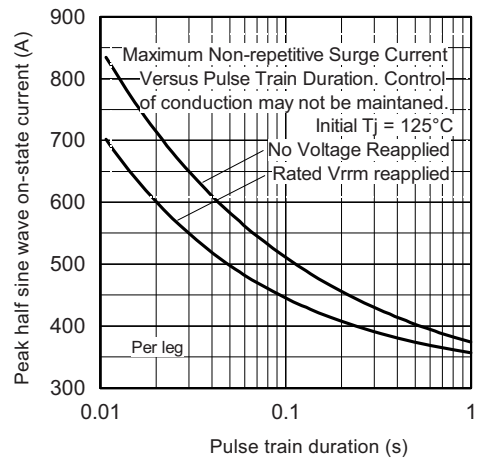


Fig. 6 - Maximum Non-Repetitive Surge Current

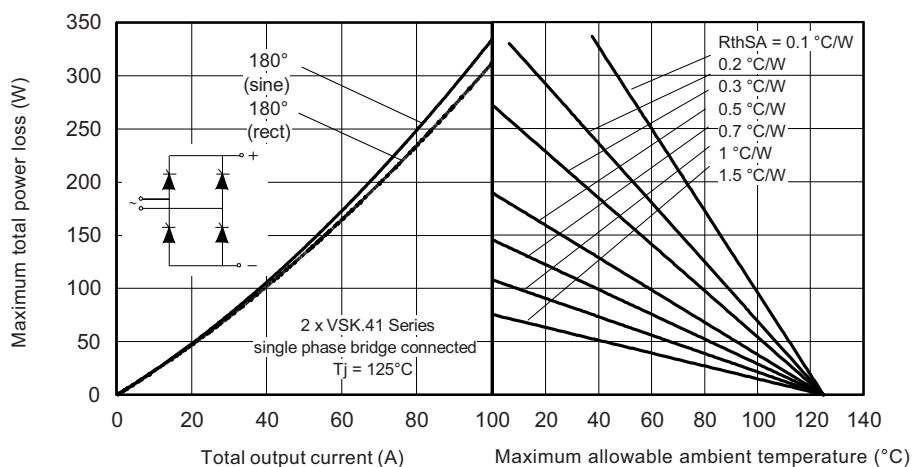


Fig. 7 - On-State Power Loss Characteristics

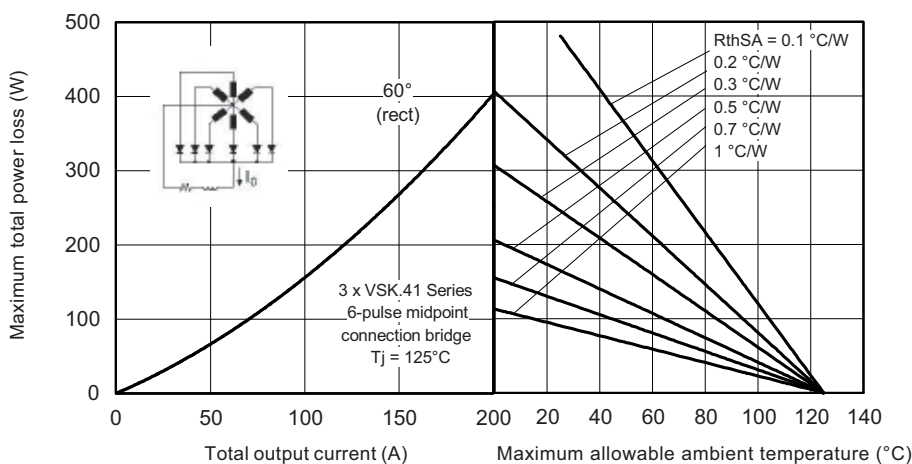


Fig. 8 - On-State Power Loss Characteristics

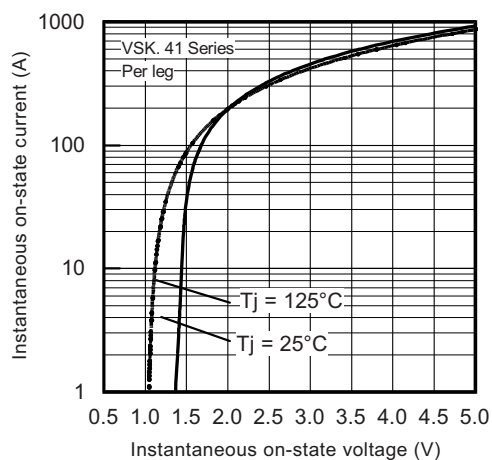


Fig. 9 - On-State Voltage Characteristics

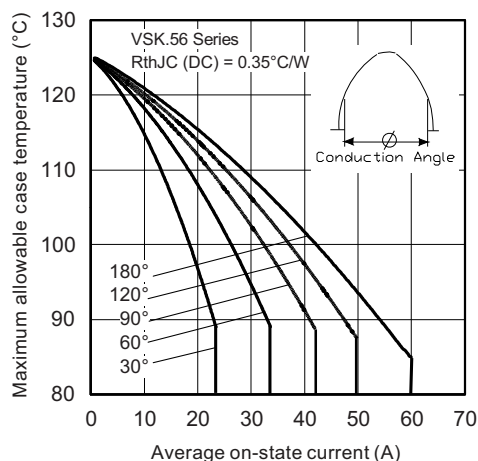


Fig. 10 - Current Ratings Characteristics

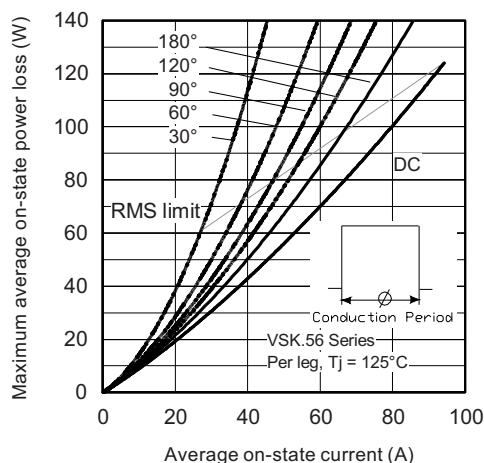


Fig. 13 - On-State Power Loss Characteristics

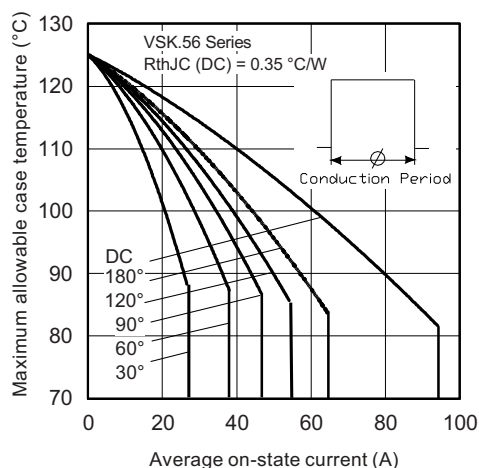


Fig. 11 - Current Ratings Characteristics

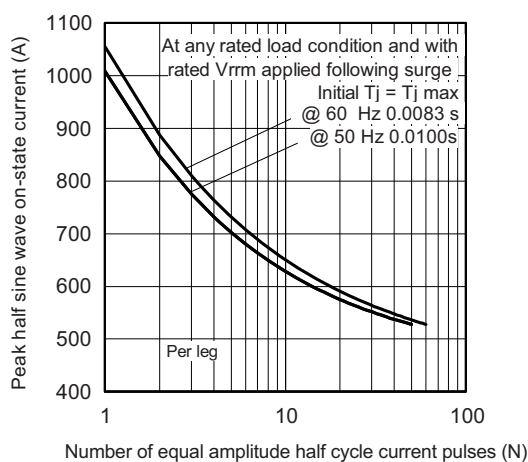


Fig. 14 - Maximum Non-Repetitive Surge Current

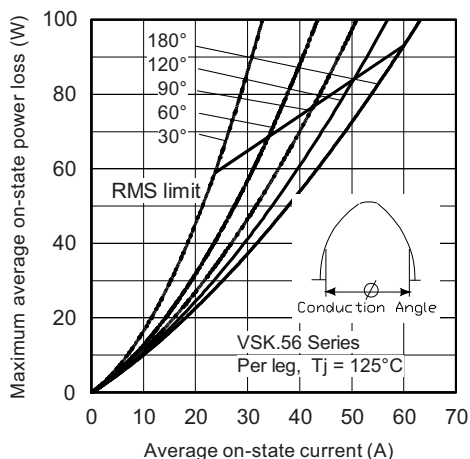


Fig. 12 - On-State Power Loss Characteristics

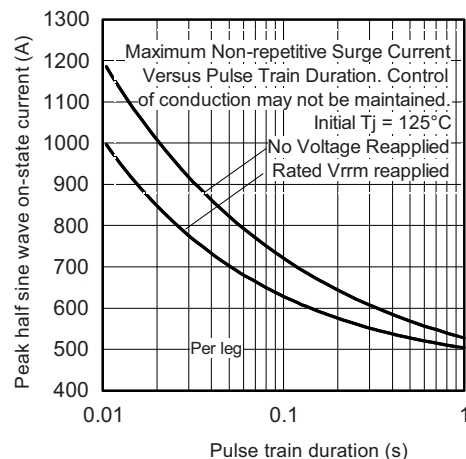


Fig. 15 - Maximum Non-Repetitive Surge Current

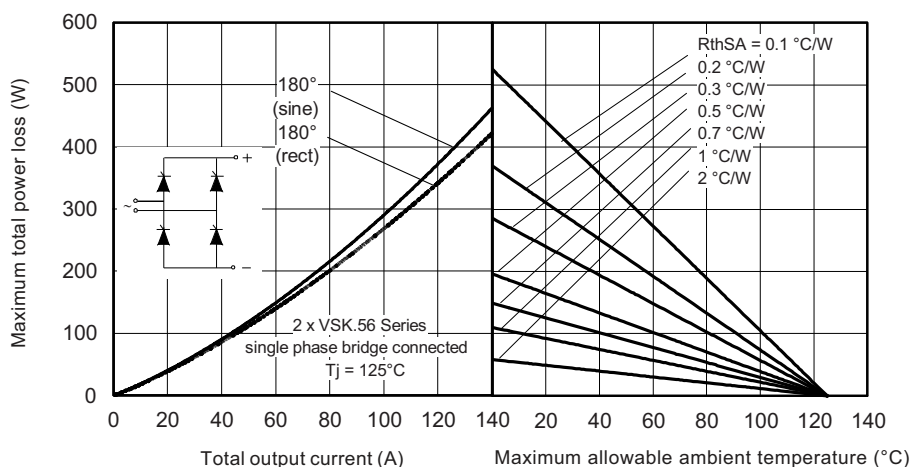


Fig. 16 - On-State Power Loss Characteristics

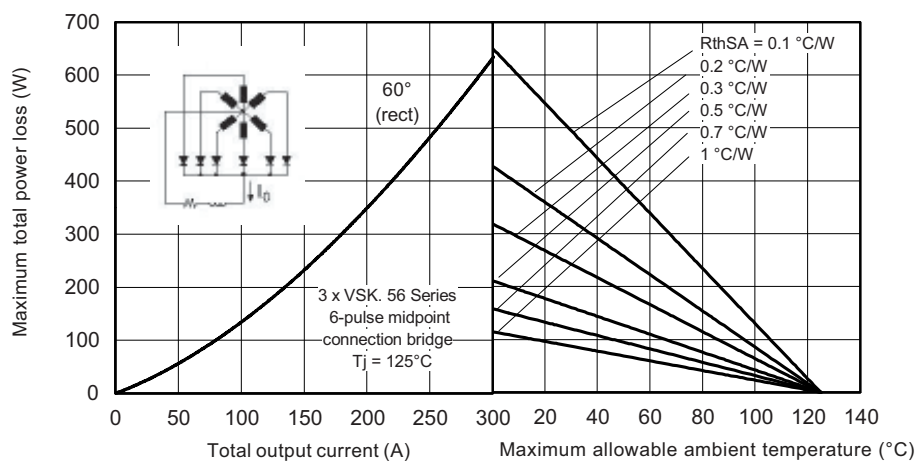


Fig. 17 - On-State Power Loss Characteristics

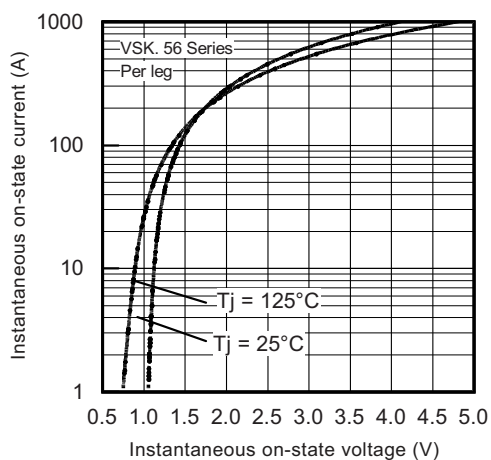


Fig. 18 - On-State Voltage Characteristics

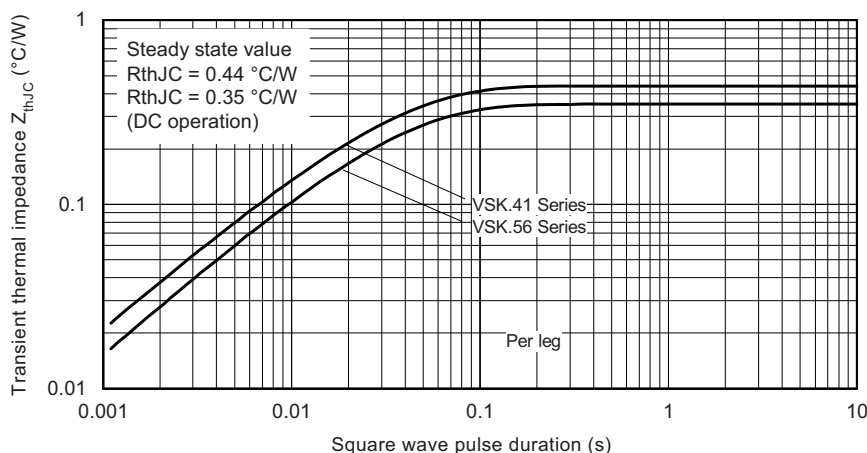


Fig. 19 - Thermal Impedance  $Z_{thJC}$  Characteristics

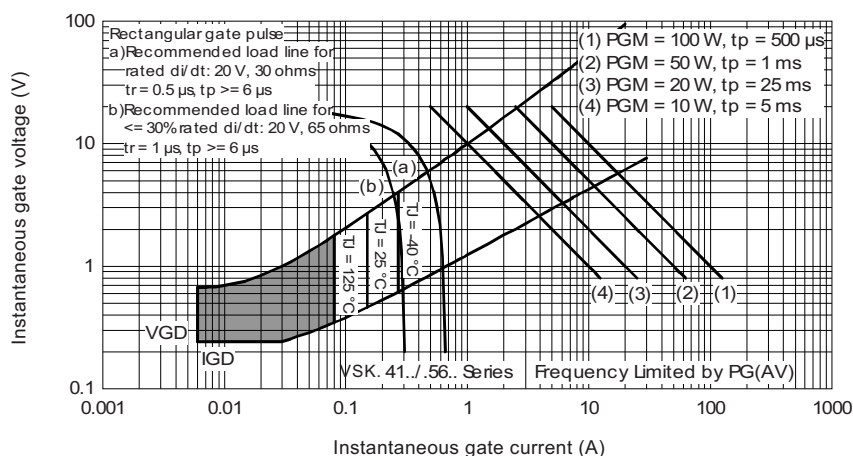


Fig. 20 - Gate Characteristics

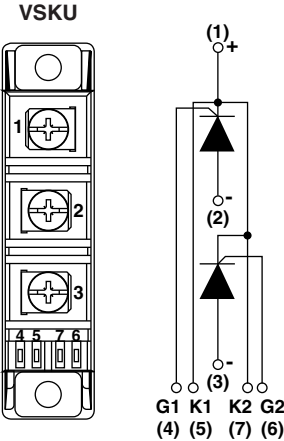
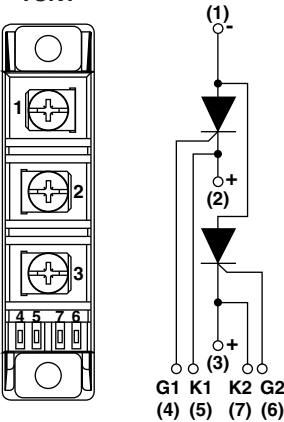
## ORDERING INFORMATION TABLE

| Device code | VS-VS                                                   | K | U | 56 | / | 16        |
|-------------|---------------------------------------------------------|---|---|----|---|-----------|
|             | 1                                                       | 2 | 3 | 4  |   | 5         |
| 1           | Vishay Semiconductors product                           |   |   |    |   |           |
| 2           | Module type                                             |   |   |    |   |           |
| 3           | Circuit configuration (see Circuit Configuration table) |   |   |    |   |           |
| 4           | Current code                                            |   |   |    |   | 41 = 45 A |
| 5           | Voltage code (see Voltage Ratings table)                |   |   |    |   | 56 = 60 A |

### Note

- To order the optional hardware go to [www.vishay.com/doc?95172](http://www.vishay.com/doc?95172)

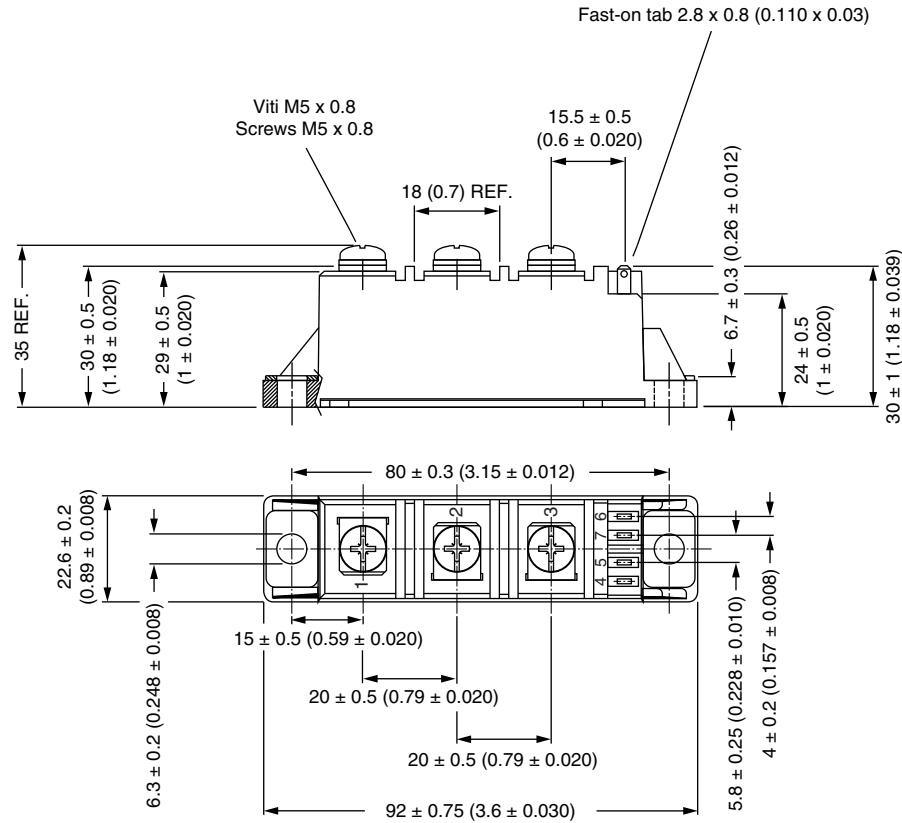


| CIRCUIT CONFIGURATION    |                            |                                                                                                         |
|--------------------------|----------------------------|---------------------------------------------------------------------------------------------------------|
| CIRCUIT DESCRIPTION      | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING                                                                                         |
| Two SCRs common cathodes | U                          | <p><b>VSKU</b></p>   |
| Two SCRs common anodes   | V                          | <p><b>VSKV</b></p>  |

| LINKS TO RELATED DOCUMENTS |                                                                        |
|----------------------------|------------------------------------------------------------------------|
| Dimensions                 | <a href="http://www.vishay.com/doc?95368">www.vishay.com/doc?95368</a> |

## ADD-A-PAK Generation VII - Thyristor

**DIMENSIONS** in millimeters (inches)





## Disclaimer

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**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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